

# Search Report

## STIC Database Tracking Number: 258994

To: STEVEN FULK Location: JEF-6A81

**Art Unit: 2891** 

Wednesday, April 30, 2008

Case Serial Number: 10/817623

From: DIANE JACKSON

Location: EIC2800 JEF-4B68 / JEF-4B68 Phone: (571)272-3260

diane.jackson@uspto.gov

### Search Notes

Attached are litigation search results in Lexis Nexis, and CourtLink and Questel-Orbit.

No Litigation was found for Serial Number 10/817623.

If you have any questions, please feel free to contact me.

Thanks,

Diane



#### Selected file: PLUSPAT

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RELOADED 02/2008 Comprehensive Worldwide Patents database
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Abstracts/Titles in English , French & German. Increased
standardization
of Assignee/Inventor names. Added cited ref's BE , CH , NL , TR , AU ,
& JPB
For PlusPat Fact Sheet , Pricing and FAQ , see the Questel website
Last update of file: 2008/04/25 (YYYY/MM/DD) 2008-17/UP (last update)

Search statement 2

nbr /pn us6346464	
PLUSPAT1 US6346460	1
PLUSPAT2 US6346461	1
PLUSPAT3 US6346462	1
PLUSPAT4 US6346463	1
PLUSPAT5 US6346464	1
PLUSPAT6 US6346465	1
PLUSPAT7 US6346466	1
PLUSPAT8 US6346467	1
PLUSPAT9 US6346468	1
PLUSPAT10US6346469	1
PLUSPAT11US634647	1
PLUSPAT12US6346470	1
PLUSPAT13US6346471	1
PLUSPAT14US6346472	1
PLUSPAT15US6346473	1
Some: numbers / Continue: Y / None: N	

Search 2 - 5 - 1 .

\*\* SS 2: Results 1

Continue: Y / N

prt full legalall max

Select All | Unselect All

1/1 PLUSPAT - Worldwide Patents - ©Questel

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US6346464 B1 20020212 [US6346464]
PN
TI
       (B1) Manufacturing method of semiconductor device
       (B1) TOKYO SHIBAURA ELECTRIC CO (JP)
PA
       Kabushiki Kaisha Toshiba, Kawasaki [JP]
PA<sub>0</sub>
       (B1) TAKEDA TORU (JP); TSUNODA TETSUJIRO (JP)
IN
       US60410000 20000627 [2000US-0604100]
AP
PR
       JP18168799 19990628 [1999JP-0181687]
IC -
       (B1) H01L-021/425
       H01L-021/265 [2006-01 A F I R M JP]
       H01L-021/261 [2006-01 A - I R M EP]
ICAA H01L-021/266 [2006-01 A - I R M EP]
       H01L-029/06 [2006-01 A - I R M EP]
       H01L-029/78 [2006-01 A - I R M EP]
       H01L-021/02 [2006 C - I R M EP]
ICCA H01L-029/02 [2006 C - I R M EP]
       H01L-029/66 [2006 C - I R M EP]
       H01L-021/261
       H01L-021/266
EC
       H01L-029/06B2B3R2
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PCL
       257E21346 257E29257 438184000 438228000 438268000 438451000
DT
       Basic
       Cited in the search report
       -US4472871(A)[US4472871]
       -US6103578(A)[US6103578]
CT
       -EP1003272(A2)[EP1003272]
       Cited by the applicant
       -US5438215(A)[US5438215]
       (B1) U.S. Patent (no pre-grant pub.) after Jan. 2, 2001
STG
       A method of manufacturing a low power dissipation semiconductor power
       device is provided which is easy to perform and suitable for mass
       production. When a first and second conductivity-type regions are formed on
       a semiconductor substrate which is selectively irradiated by impurity ions, an
       excellent super junction is formed by controlling the ion acceleration energy
       and the width of each irradiated region so that the first and second
AB
       conductivity-type regions may have a uniform impurity distribution and a
       uniform width along the direction of irradiation. Another method of
       manufacturing a low power dissipation semiconductor power device having
        an excellent super junction is provided which selectively irradiates a
       collimated neutron beam onto a P+ silicon ingot and forms an N+ region that
       has a uniform impurity distribution and a uniform width along the direction
```

US6346464 (B1) Manufacturing method of semiconductor device

of irradiation in the P+ silicon ingot.

UP 2002-08

1/1 LGST - Legal Status - ©EPO

US6346464 20001117 US/ASAASSIGNMENTOWNER: KABUSHIKI KAISHA TOSHIBA 72 HORIKAWA-CHO, SA...

PN US6346464 B1 20020212 [US6346464]

AP US60410000 20000627 [2000US-0604100]

20001117 US/AS-A ASSIGNMENT

OWNER: KABUSHIKI KAISHA TOSHIBA 72 HORIKAWA-CHO,

SAIWAI-K

ACT ASSIGNMENT OF ASSIGNORS INTEREST; ASSIGNORS: TAKEDA, TORU; TSUNODA, TETSUJIRO; REEL/FRAME: 011311/0492; SIGNING

DATES FROM 20001004 TO 20001005

20040810 US/RF-A

REISSUE APPLICATION FILED EFFECTIVE DATE: 20040405

UP 2004-34

1/1 CRXX - US Claims
Reassignations - @CLAIMS/RRX

US6346464 20040405 REISSUE REQUESTEDISSUE DATE OF O.G.: 20040810REISSUE REQUEST NUMBER...

AN 3637331

PN 6,346,464 A 20020212 [US6346464]

PA Toshiba Corp JP PT C (Chemical)

20040405 REISSUE REQUESTED ISSUE DATE OF O.G.: 20040810

REISSUE REQUEST NUMBER: 10/817623

ACT EXAMINATION GROUP RESPONSIBLE FOR REISSUEPROCESS: 2812

### Reissue Patent Number:

UP 2004-33 UACT 2004-08-10

Selected file: FAMPAT

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RELOADED 02/2008 Searchable bibliographic & abstracts-all family members
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Search & display options for both FamPat & extended family definition Coverage: 78 patenting authorities; start dates vary from 1800 forward Abstracts/Titles in English , French & German. Increased standardization

of Assignee/Inventor names. Added cited ref's BE , CH , NL , TR , AU , & JPB

For more details , see the FamPat Fact Sheet and Questel website Last update of file: 2008/04/25 (YYYY/MM/DD) 2008-17/UP (last update)

Search statement 1

### nbr/pn us6346464

FAMPAT1 US6346460	1
FAMPAT2 US6346461	1
FAMPAT3 US6346462	1
FAMPAT4 US6346463	1
FAMPAT5 US6346464	1
FAMPAT6 US6346465	1
FAMPAT7 US6346466	1
FAMPAT8 US6346467	1
FAMPAT9 US6346468	1
FAMPAT10US6346469	1
FAMPAT11US634647	1
FAMPAT12US6346470	1
FAMPAT13US6346471	1
FAMPAT14US6346472	1
FAMPAT15US6346473	1
Some: numbers / Continue: Y / None: N	

Search 1 - 5 - 1

\*\* SS 1: Results 1

Continue: Y / N

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JP2001015448 Manufacturing method of semiconductor device
FAN
      20042792240325
         JP2001015448 A 20010119 [JP2001015448]
PN
                      B1 20020212 [US6346464]
         US6346464
         JP3851744
                      B2 20061129 [JP3851744]
TI
      Manufacturing method of semiconductor device
PA
      TOKYO SHIBAURA ELECTRIC CO
PA0
      Kabushiki Kaisha Toshiba, Kawasaki [JP]
IN
      TAKEDA TORU; TSUNODA TETSUJIRO
      1999JP-0181687 19990628
AP
      2000US-0604100 20000627
PR
      1999JP-0181687 19990628
      H01L-021/02
      H01L-021/261
      H01L-021/265
      H01L-021/266
IC ·
      H01L-021/425
      H01L-029/02
      H01L-029/06
      H01L-029/66
      H01L-029/78
      H01L-021/265 [2006-01 A F I R M JP]
      H01L-021/261 [2006-01 A - I R M EP]
ICAA H01L-021/266 [2006-01 A - I R M EP]
      H01L-029/06 [2006-01 A - I R M EP]
      H01L-029/78 [2006-01 A - I R M EP]
      H01L-021/02 [2006 C - I R M EP]
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      H01L-029/66 [2006 C - I R M EP]
      H01L-021/261
      H01L-021/266
EC
      H01L-029/06B2B3R2
      H01L-029/78B2
      ORIGINAL (O): 438514000; CROSS-REFERENCE (X): 257E21330
PCL
      257E21346 257E29257 438184000 438228000 438268000 438451000
      H01L21/265 F; H01L21/26 N; H01L21/265 M
FI
      (US6346464)
CT
      Cited in the search report
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-US4472871(A)[US4472871] -US6103578(A)[US6103578]

-EP1003272(A2)[EP1003272]

Cited by the applicant

-US5438215(A)[US5438215] (JP2001015448)

(A)

[19] Citation as reason for refusal of an application

- JP (A) 2000208527 [JP2000208527]
- JP (A) 1981069823 [JP56069823]
- JP (A) 1998223896 [JP10223896]

(US6346464)

A method of manufacturing a low power dissipation semiconductor power device is provided which is easy to perform and suitable for mass production. When a first and second conductivity-type regions are formed on a semiconductor substrate which is selectively irradiated by impurity ions, an excellent super junction is formed by controlling the ion acceleration energy and the width of each irradiated region so that the first and second conductivity-type regions may have a uniform impurity distribution and a uniform width along the direction of irradiation. Another method of manufacturing a low power dissipation semiconductor power device having an excellent super junction is provided which selectively irradiates a collimated neutron beam onto a P+ silicon ingot and forms an N+ region that has a uniform impurity distribution and a uniform width along the direction of irradiation in the P+ silicon ingot.

AB

CT

uniform along the direction of irradiation.

The present invention is a semiconductor device manufacturing method of forming a first and second conductivity-type regions by irradiating impurity ions selectively onto a semiconductor substrate; wherein two shielding masks in a reversed imaging relation to each other are used to restrict the impurity ion irradiated regions so that the cross-sectional shape and the cross-section area of the first and second conductivity-type regions on planes vertical to the irradiation direction may be uniform in the direction of irradiation; and the impurity ion acceleration energy is controlled to make the impurity concentration in the first and second conductivity-type regions uniform in the direction of irradiation.

The present invention is a semiconductor device manufacturing method of forming an N+ region by selectively irradiating a neutron beam onto a P+ semiconductor ingot, wherein the incident angle of the neutron beam is collimated so that the cross-sectional shape and the cross-section area of the N+ region may be uniform in the direction of irradiation and so that the impurity concentration in the N+ region may be uniform in the direction of irradiation.

(US6346464)

The present invention has been made to solve the above problem and its principal object is to provide a method of manufacturing low power dissipation semiconductor power devices having the super junction structure. The present invention allows the use of semiconductor ingots made of group IV elements such as germanium and silicon carbide.

Specifically, the ion implantation and the neutron beam irradiation have the following advantages:

(1) Since a selective irradiation can be performed by an electric or magnetic sweep or movement of silicon substrate, the width of irradiation pattern can be continuously controlled according to changes in ion acceleration energy, and the vertical distribution of implanted ions shows an excellent uniformity. A shortcoming in the above prior art is that such manufacturing method of repeating the epitaxial growth process to create low power dissipation semiconductor power devices is costly, difficult to implement and not suitable for mass production.

As described above, by the method of forming a super junction according to the present invention, which does not use conventional complex processes like the epitaxial growth but use only efficient processes such as ion implantation and neutron beam irradiation, a super junction can be formed that has an arbitrary and uniform cross-section in the vertical direction. (US6346464)

1. A semiconductor device manufacturing method of forming a second conductivity-type region by irradiating impurity ions onto a first ICLM conductivity-type semiconductor substrate;

wherein the impurity ion irradiated region is restricted by a shield mask intercepting said impurity ions and the impurity ion acceleration energy is controlled to provide a uniform impurity distribution in the direction of

ADB

irradiation in said second conductivity-type region.

- 2. A semiconductor device manufacturing method of forming at least one of a first and second conductivity-type regions in a semiconductor substrate by selectively irradiating impurity ions onto said semiconductor substrate; wherein the impurity distributions in said first and second conductivity-type regions are uniform in the direction of irradiation, and the impurity ion acceleration energy and the area of each region irradiated by said impurity ions are controlled so that the cross-sectional shape and cross-section area of said first and second conductivity-type regions on planes perpendicular to the direction of irradiation may be uniform in the direction of irradiation.
- 12. A semiconductor device manufacturing method of forming a first conductivity-type region and a second conductivity-type region on a semiconductor substrate by irradiating impurity ions onto said semiconductor substrate;

wherein the regions irradiated by impurity ions are restricted by impurity ion intercepting shield masks which are in an inverted imaging relation to each other so that the cross-sectional shape and the cross-section area of the first and second conductivity-type regions on planes perpendicular to the direction of irradiation may be uniform along the direction of irradiation, and the impurity ion acceleration energy is controlled to make the impurity ion distributions in the first and second conductivity-type regions uniform along the direction of irradiation.

14. A semiconductor device manufacturing method of forming an N+ region by irradiating a neutron beam onto a semiconductor ingot having a P+ region;

wherein the incident direction of said neutron beam is collimated to make the cross-sectional shape and the cross-section area of said N+ region on planes perpendicular to the direction of irradiation uniform along the direction of irradiation, and the impurity distribution in said N+ region is controlled to be uniform along the direction of irradiation.

UP 2002-08

口 1/1 LGST - Legal 区 Status - ©EPO

US6346464 20001117 US/ASAASSIGNMENTOWNER: KABUSHIKI KAISHA TOSHIBA 72 HORIKAWA-CHO, SA...

PN US6346464 B1 20020212 [US6346464]

AP US60410000 20000627 [2000US-0604100]

20001117 US/AS-A

ACT ASSIGNMENT
OWNER: KABUSHIKI KAISHA TOSHIBA 72 HORIKAWA-CHO,
SAIWAI-K

ASSIGNMENT OF ASSIGNORS INTEREST; ASSIGNORS: TAKEDA, TORU; TSUNODA, TETSUJIRO; REEL/FRAME: 011311/0492; SIGNING DATES FROM 20001004 TO 20001005 20040810 US/RF-A REISSUE APPLICATION FILED EFFECTIVE DATE: 20040405 2004-34

1/1 CRXX - US Claims
Reassignations - @CLAIMS/RRX

US6346464 20040405 REISSUE REQUESTEDISSUE DATE OF O.G.: 20040810REISSUE REQUEST NUMBER...

AN 3637331

UP

PN 6,346,464 A 20020212 [US6346464]

PA Toshiba Corp JP PT C (Chemical)

20040405 REISSUE REQUESTED ISSUE DATE OF O.G.: 20040810

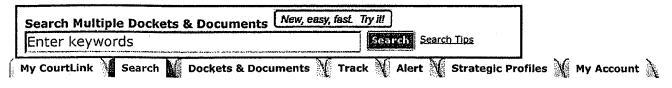
REISSUE REQUEST NUMBER: 10/817623

· ACT EXAMINATION GROUP RESPONSIBLE FOR REISSUEPROCESS: 2812

### Reissue Patent Number:

UP 2004-33 UACT 2004-08-10 LexisNexis CourtLink

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Patent Search 6346464 4/30/2008

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604100 (09) 6346464 February 12, 2002

### UNITED STATES PATENT AND TRADEMARK OFFICE GRANTED PATENT

### 6346464

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# Order Patent File History / Wrapper from REEDFAX® Link to Claims Section

February 12, 2002

### Manufacturing method of semiconductor device

**REISSUE:** April 5, 2004 - Reissue Application filed Ex. Gp.: 2812; Re. S.N. 10/817,623 (O.G. August 10, 2004)

INVENTOR: Takeda, Toru - Kokubunji, Japan (JP); Tsunoda, Tetsujiro - Urawa, Japan (JP)

**APPL-NO:** 604100 (09)

FILED-DATE: June 27, 2000

**GRANTED-DATE:** February 12, 2002

**PRIORITY:** June 28, 1999 - 11181687, Japan (JP)

ASSIGNEE-PRE-ISSUE: November 17, 2000 - ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS)., KABUSHIKI KAISHA TOSHIBA 72 HORIKAWA-CHO, SAIWAI-KUKAWASAKI-SHI, (1), Reel and Frame Number: 011311/0492

**ASSIGNEE-AT-ISSUE:** Kabushiki Kaisha Toshiba, Kawasaki, Japan (JP), Foreign company or corporation (03)

LEGAL-REP: Oblon, Spivak, McClelland, Maier & Neustadt, P.C.

PUB-TYPE: February 12, 2002 - Utility Patent having no previously published pre-grant publication (B1)

**PUB-COUNTRY:** United States (US)

**US-MAIN-CL:** 438#514

US-ADDL-CL: 257#E21.33, 257#E21.346, 257#E29.257, 438#184, 438#228, 438#268, 438#451

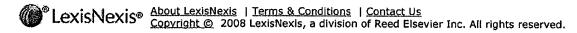
CL: 438, 257

SEARCH-FLD: 438#514, 438#268, 438#184, 438#270, 438#299, 438#302, 438#303, 438#305,

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(6346464 or 6,346,464)  Suggest Terms for My Search  Check Spelling	and and or or w/N within N words pre/N precedes by N words w/p in same paragraph
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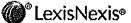
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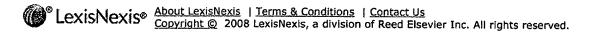
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LENGTH: 771 words

**HEADLINE:** Barclays PLC → Rule 8.3 - SAINSBURY(J)

**BODY:** 

**FORM 8.3** 

DEALINGS BY PERSONS WITH INTERESTS IN SECURITIES REPRESENTING 1% OR MORE

(Rule 8.3 of the City Code on Takeovers and Mergers)

1. KEY INFORMATION

Name of person dealing BARCLAYS PLC +

(Note 1)

Company dealt in SAINSBURY(J)

Class of relevant security ORD GBP0.28571428

to which the dealings being

disclosed relate (Note 2)

Date of dealing 17 August 2007

- 2. INTERESTS, SHORT POSITIONS AND RIGHTS TO SUBSCRIBE
- (a) Interests and short positions (following dealing) in the class of relevant security dealt in (Note 3)

Long Short

Number

Number

(%)

(1) Relevant

62,693,536

(%) 3.60%

2,296,378

0.13%

securities

(2) Derivatives **6,346,464** 0.36% 6,846,869 0.39%

(other than options)

(3) Options and 2,750 0.00% 0 0.00%

agreements to

purchase/sell

Total 69,042,750 3.96% 9,143,247 0.52%

(b) Interests and short positions in relevant securities of the company, other

than the class dealt in (Note 3)

Class of Long Short

relevant

security:

Number (%) Number (%)

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⊕ ☐ TITLE 43. PUBLIC LANDS

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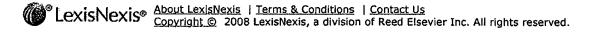
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